

Vishay Semiconductors

Small Signal Fast Switching Diodes

Features

- Silicon epitaxial planar diodes
- Electrically equivalent diodes: 1N4148 - 1N914
- Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC
- Halogen-free according to IEC 61249-2-21 definition







Applications

· Extreme fast switches

Mechanical Data

Case: DO-35

Weight: approx. 105 mg
Cathode band color: black
Packaging codes/options:

TR/10K per 13" reel (52 mm tape), 50K/box TAP/10K per ammopack (52 mm tape), 50K/box

Parts Table

Part	Ordering code	Type marking	Remarks	
1N4148	1N4148-TAP or 1N4148-TR	V4148	Ammopack/tape and reel	

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Repetitive peak reverse voltage		V _{RRM}	100	V
Reverse voltage		V _R	75	V
Peak forward surge current	t _p = 1 μs	I _{FSM}	2	А
Repetitive peak forward current		I _{FRM}	500	mA
Forward continuous current		I _F	300	mA
Average forward current	V _R = 0	I _{FAV}	150	mA
Power dissipation	I = 4 mm, T _L = 45 °C	P _{tot}	440	mW
	$I = 4$ mm, $T_L \le 25$ °C	P _{tot}	500	mW

Thermal Characteristics

T_{amb} = 25 °C, unless otherwise specified

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Parameter	Test condition	Symbol	Value	Unit
Thermal resistance junction to ambient air	I = 4 mm, T _L = constant	R _{thJA}	350	K/W
Junction temperature		T _j	175	°C
Storage temperature range		T _{stg}	- 65 to + 150	°C

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Electrical Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min.	Тур.	Max.	Unit
Forward voltage	I _F = 10 mA	V _F			1000	mV
Reverse current	V _R = 20 V	I _R			25	nA
	V _R = 20 V, T _j = 150 °C	I _R			50	μΑ
	V _R = 75 V	I _R			5	μΑ
Breakdown voltage	$I_R = 100 \mu A, t_p/T = 0.01,$ $t_p = 0.3 \text{ ms}$	V _(BR)	100			V
Diode capacitance	$V_R = 0$, $f = 1$ MHz, $V_{HF} = 50$ mV	C _D			4	pF
Rectification efficiency	V _{HF} = 2 V, f = 100 MHz	η_r	45			%
Reverse recovery time	$I_F = I_R = 10 \text{ mA}, i_R = 1 \text{ mA}$	t _{rr}			8	ns
	$I_F = 10 \text{ mA}, V_R = 6 \text{ V},$ $I_R = 0.1 \text{ x } I_R, R_L = 100 \Omega$	t _{rr}			4	ns

Typical Characteristics

T_{amb} = 25 °C, unless otherwise specified

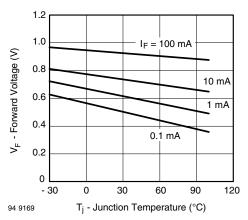


Figure 1. Forward Voltage vs. Junction Temperature

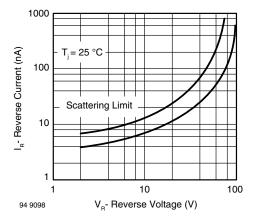


Figure 3. Reverse Current vs. Reverse Voltage

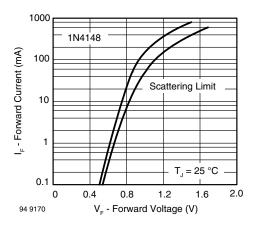


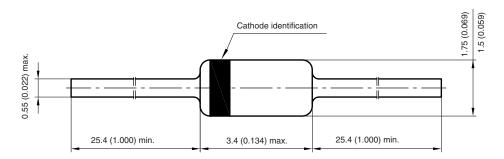
Figure 2. Forward Current vs. Forward Voltage

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Package Dimensions in millimeters (inches): DO-35_02



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